

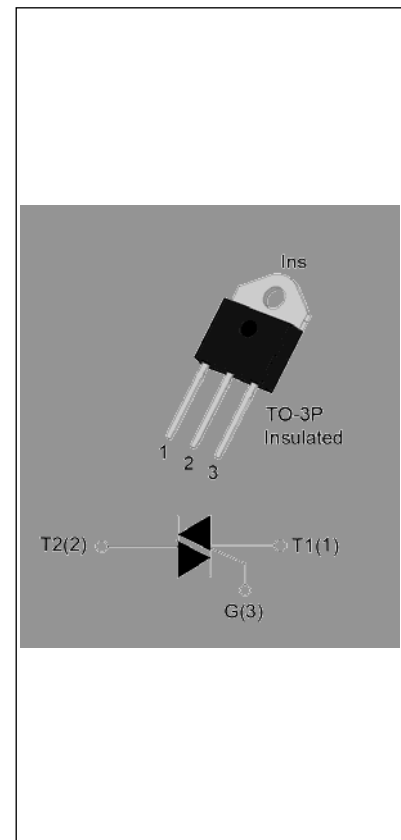


## DESCRIPTION:

The T3035H-6Z triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T3035H-6Z provides a very high switching capability up to junction temperatures of 150°C. By using an internal ceramic pad, T3035H-6Z provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.

## MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	30	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT} / /$	35/35/35	mA



## ABSOLUTE MAXIMUM RATINGS

Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-150	
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	600	V
RMS on-state current ( $T_c = 114^\circ\text{C}$ )	$I_{T(RMS)}$	30	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	270	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		297	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	365	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=150^\circ\text{C}$ )	$di/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=150^\circ\text{C}$ )	$I_{GM}$	4	A



Average gate power dissipation ( $T_j=150$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1	kV

### ELECTRICAL CHARACTERISTICS ( $T_j=25$ unless otherwise specified)

$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	35	mA
$V_{GT}$		- -	MAX.	1.3	V
$V_{GD}$	$V_D=V_{DRM} T_j=150$ $R_L=3.3K$	- -	MIN.	0.15	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	70	mA
				80	
$I_H$	$I_T=500mA$		MAX.	50	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150$		MIN.	1200	V/ $\mu s$
(dI/dt) <sub>c</sub>	(dV/dt) <sub>c</sub> =20V/ $\mu s$ , $T_j=150$		MIN.	18	A/ms
$t_{on}$	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	10	$\mu s$
$t_{off}$				80	

### STATIC CHARACTERISTICS

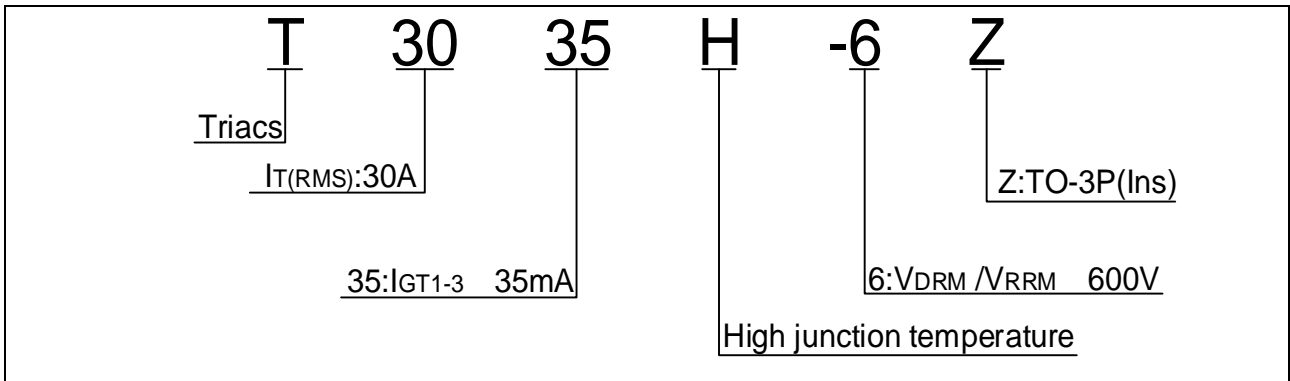
$V_{TM}$	$I_{TM}=42A t_p=380\mu s$	$T_j=25$		1.5	V
$V_{TO}$	Threshold voltage	$T_j=150$		0.7	V
$R_D$	Dynamic resistance	$T_j=150$		16	m
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$		5	$\mu A$
$I_{RRM}$		$T_j=150$		5	mA

### THERMAL RESISTANCES

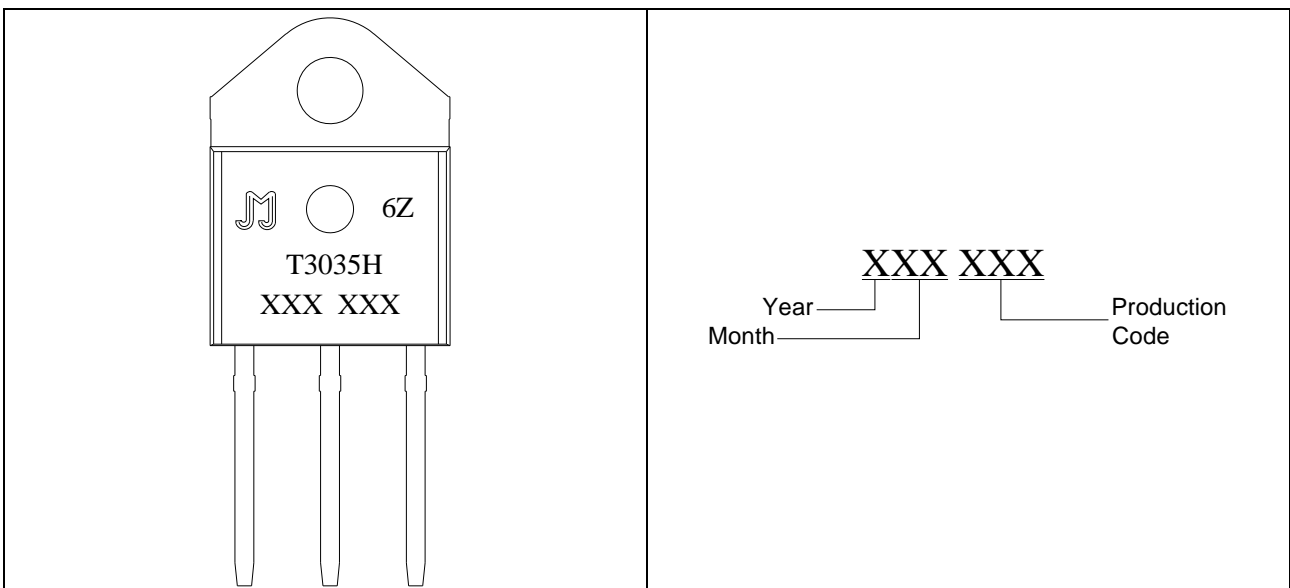
$R_{th(j-c)}$	junction to case (AC)			0.85	/W
$R_{th(j-a)}$	junction to ambient (AC)			50	/W



## ORDERING INFORMATION

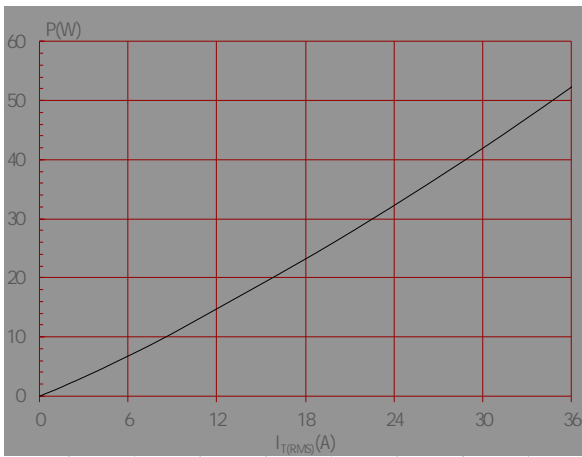


## MARKING

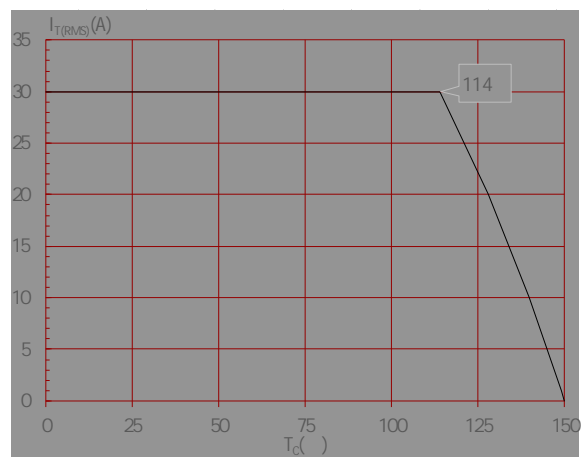




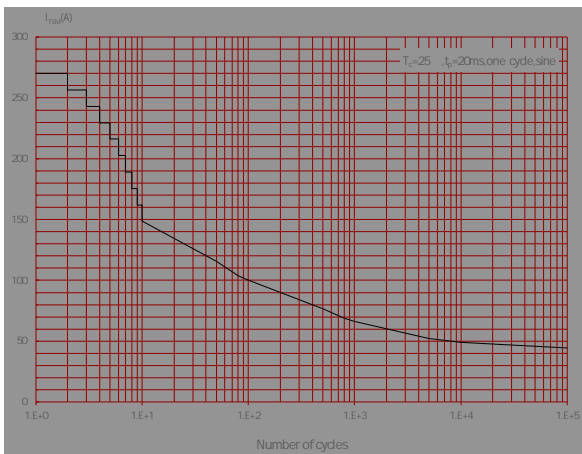
Maximum power dissipation versus RMS on-state current



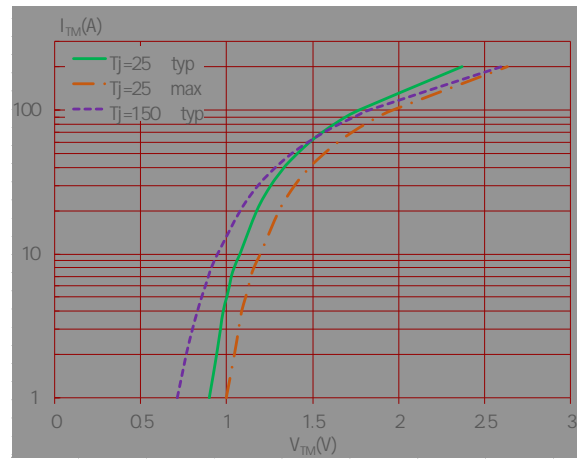
RMS on-state current versus case temperature



Surge peak on-state current versus number of cycles



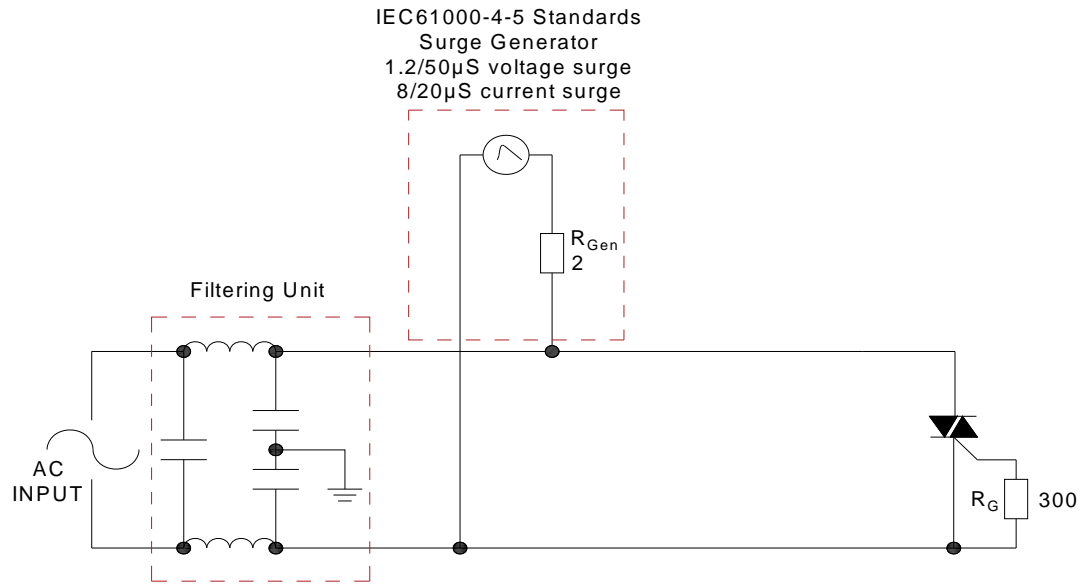
On-state characteristics



Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20$ ms, and corresponding value of  $I^2$



FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie



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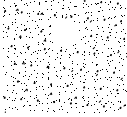
## ORDERING INFORMATION


Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated



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## PACKAGE MECHANICAL DATA





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